Common Cathode Silicon Dual Switching Diode

This Common Cathode Silicon Epitaxial Planar Dual Diode is designed for use in ultra high speed switching applications. This device is housed in the SOT-416/SC-90 package which is designed for low power surface mount applications, where board space is at a premium.

Features

- Fast trr
- Low C_D
- Pb–Free Packages are Available

Rating	Symbol	Value	Unit	
Reverse Voltage	V _R	80	Vdc	
Peak Reverse Voltage	V _{RM}	80	Vdc	
Forward Current	١ _F	100	mAdc	
Peak Forward Current	I _{FM}	300	mAdc	
Peak Forward Surge Current (Note 1)	I _{FSM}	2.0	Adc	

MAXIMUM RATINGS ($T_{\Lambda} = 25^{\circ}C$)

THERMAL CHARACTERISTICS

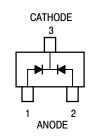
Characteristic	Symbol	Max	Unit
Power Dissipation	PD	150	mW
Junction Temperature	TJ	150	°C/W
Storage Temperature Range	T _{stg}	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability. 1. $t = 1 \mu S$



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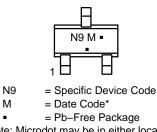
http://onsemi.com





SC-75/SOT-416 **CASE 463** STYLE 3

MARKING DIAGRAM



(Note: Microdot may be in either location) *Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
DAN222	SC-75/SOT-416	3000/Tape & Reel
DAN222G	SC-75/SOT-416 (Pb-Free)	3000/Tape & Reel
DAN222T1	SC-75/SOT-416	3000/Tape & Reel
DAN222T1G	SC-75/SOT-416 (Pb-Free)	3000/Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

	()())				
Characteristic	Symbol	Condition	Min	Max	Unit
Reverse Voltage Leakage Current	I _R	V _R = 70 V	-	0.1	μAdc
Forward Voltage	VF	I _F = 100 mA	-	1.2	Vdc
Reverse Breakdown Voltage	V _R	I _R = 100 μA	80	-	Vdc
Diode Capacitance	CD	V _R = 6.0 V, f = 1.0 MHz	-	3.5	pF
Reverse Recovery Time	t _{rr} (2)	I_F = 5.0 mA, V_R = 6.0 V, R_L = 100 Ω,I_{rr} = 0.1 I_R	-	4.0	ns

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$)

2. t_{rr} Test Circuit on following page.

TYPICAL ELECTRICAL CHARACTERISTICS

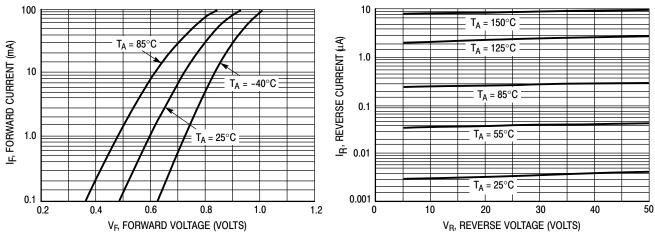


Figure 1. Forward Voltage

Figure 2. Reverse Current

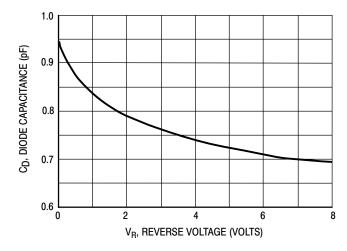


Figure 3. Diode Capacitance

DAN222

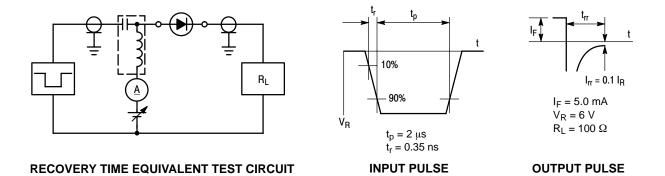
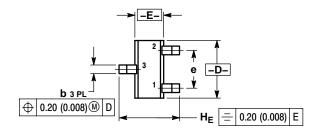


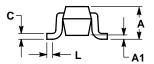
Figure 4. Reverse Recovery Time Test Circuit for the DAN222

DAN222

PACKAGE DIMENSIONS

SC-75/SOT-416 CASE 463-01 ISSUE F





NOTES:

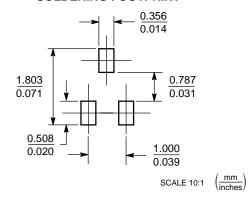
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2.	CONTROLLING	DIMENSION:	MILLIMETER.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
С	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.059	0.063	0.067
E	0.70	0.80	0.90	0.027	0.031	0.035
е	1.00 BSC			C	.04 BSC	~
L	0.10	0.15	0.20	0.004	0.006	0.008
HE	1.50	1.60	1.70	0.061	0.063	0.065

STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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